

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning at line 17 of page 5 with the following amended paragraph:

Each sample of the layer structure was formed by the steps of growing a 100-nm-thick AlAs layer 82 on a GaAs substrate 80, and growing a 1- μ m-thick GaAs layer 84 thereon. The samples of the layer structure before the oxidation are shown in Fig. 3A in cross section, whereas the samples of layer structure after the oxidation are shown in Fig. 3B in cross section. Each sample had a cleaved surface 90 from which the oxidation proceeds. The layer structure shown in Fig. 3B had a pair of stripe Al-oxidized areas 88 in the AlAs layer 82 adjacent to the cleaved surfaces 90 and an Al-nonoxidized area 86 sandwiched between the pair of Al-oxidized areas 88 after the selective oxidation. Each sample of the layer structure was cleaved to expose the cleaved surface 90 just before the selective oxidation. The selective oxidation was conducted as follows.